

For Further Growth Together

SN1210G3

SiC Schottky Barrier Diode

Features

- Silicon Carbide Schottky Barrier Diode
- Small die size
- High IFSM
- Low IR
- High-Recovery Speed

Applications

- Switch mode power supplies
- Power Factor Correction
- Secondary Side Rectification
- PV Power Conditioners

Maximim Ratings (Ta=25℃)

Parameter	Symbol	Conditions	Limit	Unit
Repetitive peak reverse voltage	VRM		1200	V
Reverse voltage (DC)	VR		1200	V
Forward current (DC)	lF		10	Α
Surge no repetitive forward current	Ifsм	10ms Sinusoidal	100	Α
Junction temperature	Tj		175	°C
Storage temperature	Tstg		-55 to +175	°C

Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
DC blocking voltage	VDC	Ir=0.2mA	1200	-	-	V
Forward voltage	VF	I⊧=10A, Ta=25℃	-	1.48	1.88	V
		I _F =10A, Ta=150°C	-	2.15	-	V
		I⊧=10A, Ta=175°C	-	2.36	-	V
Reverse current	lr	VR=1200V, Ta=25°C	-	0.1	200	uA
		VR=1200V, Ta=150°C	-	1.2	-	uA
		VR=1200V, Ta=175℃	-	3.5	-	uA
Junction capacitance	С	V _R =1V, f=1MHz	-	450	-	pF
Total capacitive charge	Qc	VR=800V, di/dt=500A/us	-	34	-	nC
Switching time	tc	VR=800V, di/dt=500A/us	-	15	-	ns

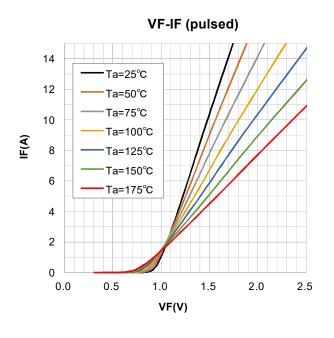


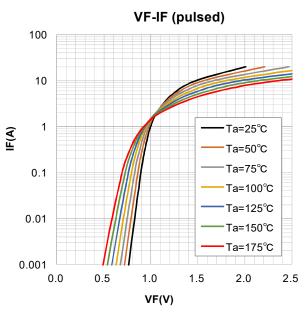


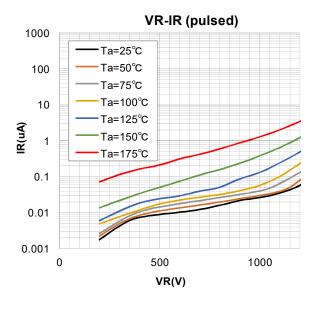
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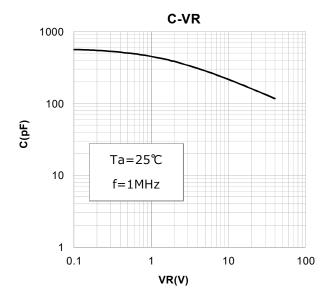
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Electrical Characteristics curves











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NOTE

- 1) This document is for reference only.
- 2) Please request for the specification sheet before use.
- 3) Since the products are in wafer form, the values in this document are for reference only.
- 4) Although we strive to improve the quality of our products, they may malfunction or fail. When using this product, please implement a safety design suitable for the system within your responsibility.
- 5) Although this document has been prepared with great care, we assume no responsibility for any damages incurred due to errors in the provoded information.
- 6) If the operating environment (e.g., high temperature, high voltage, high current) is severe, the reverse current may become excessively large and the device may be destroyed due to the increased reverse
- 7) The absolute maximum ratings must not be exceeded even momentarily. Do not exceed the absolute maximum ratings for any of the multiple ratings.
- 8) In particular, when evaluating or using the product in a resin-encapsulated package or in a sealed environment, be sure to measure the temperature and confirm that the maximum junction temperature designated as the maximum ratings is not exceeded.
- 9) The products described in this document are intended for use in general electronic equipment (e.g., AV equipment, OA equipment, home appliances).
- 10) This product is not intended for use in products whose manufacture, use, or sale is prohibited by domestic or foreign laws or regulations.
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- 12) When exporting this product, please comply with applicable export laws and regulations and follow the necessary procedures.
- 13) The information in this document is subject to change without notice.
- 14) The process flow and process conditions of this product are subject to change without notice.